Piotr Perlin

List of Publications by Citations

200 papers	3,605 citations	27 h-index	54 g-index
258 ext. papers	3,995 ext. citations	2.4 avg, IF	4.55 L-index

#	Paper	IF	Citations
200	Raman scattering and x-ray-absorption spectroscopy in gallium nitride under high pressure. *Physical Review B*, **1992**, 45, 83-89	3.3	498
199	Blue temperature-induced shift and band-tail emission in InGaN-based light sources. *Applied Physics Letters*, **1997**, 71, 569-571	3.4	455
198	Low-temperature study of current and electroluminescence in InGaN/AlGaN/GaN double-heterostructure blue light-emitting diodes. *Applied Physics Letters*, **1996**, 69, 1680-1682	3.4	146
197	Raman-scattering studies of aluminum nitride at high pressure. *Physical Review B*, **1993**, 47, 2874-2877	3.3	116
196	InGaN/GaN quantum wells studied by high pressure, variable temperature, and excitation power spectroscopy. *Applied Physics Letters*, **1998**, 73, 2778-2780	3.4	88
195	Visible light communications using a directly modulated 422 nm GaN laser diode. *Optics Letters*, **2013**, 38, 3792-4	3	86
194	Influence of pressure on photoluminescence and electroluminescence in GaN/InGaN/AlGaN quantum wells. *Applied Physics Letters*, **1997**, 70, 2993-2995	3.4	83
193	Reduction of the energy gap pressure coefficient of GaN due to the constraining presence of the sapphire substrate. *Journal of Applied Physics*, **1999**, 85, 2385-2389	2.5	78
192	Pressure and temperature dependence of the absorption edge of a thick Ga0.92In0.08As0.985N0.015 layer. *Applied Physics Letters*, **1998**, 73, 3703-3705	3.4	66
191	Degradation mechanisms in InGaN laser diodes grown on bulk GaN crystals. *Applied Physics Letters*, **2006**, 88, 201111	3.4	64
190	Bulk GaN crystal growth by the high-pressure ammonothermal method. *Journal of Crystal Growth*, **2007**, 300, 11-16	1.6	63
189	Blue-violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular-beam epitaxy. *Applied Physics Letters*, **2005**, 86, 011114	3.4	62
188	Interband optical absorption in free standing layer of Ga0.96In0.04As0.99N0.01. *Applied Physics Letters*, **2000**, 76, 1279-1281	3.4	62
187	Single-quantum well InGaN green light emitting diode degradation under high electrical stress. *Microelectronics Reliability*, **1999**, 39, 1219-1227	1.2	51
186	Growth of 1.3 μm InGaAsN laser material on GaAs by molecular beam epitaxy. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1999**, 17, 1272		48
185	The effects of indium concentration and well-thickness on the mechanisms of radiative recombination in InxGa1−xN quantum wells. *MRS Internet Journal of Nitride Semiconductor Research* , **2000**, 5, 1		46
184	Effect of internal absorption on cathodoluminescence from GaN. *MRS Internet Journal of Nitride Semiconductor Research*, **1998**, 3, 1		46

183	60mW continuous-wave operation of InGaN laser diodes made by plasma-assisted molecular-beam epitaxy. *Applied Physics Letters*, **2006**, 88, 221108	3.4	45
182	Role of the electron blocking layer in the low-temperature collapse of electroluminescence in nitride light-emitting diodes. *Applied Physics Letters*, **2007**, 90, 103507	3.4	44
181	Optically pumped 500 nm InGaN green lasers grown by plasma-assisted molecular beam epitaxy. *Journal of Applied Physics*, **2011**, 110, 063110	2.5	39
180	Fully-screened polarization-induced electric fields in blue□violet InGaN□GaN light-emitting devices grown on bulk GaN. *Applied Physics Letters*, **2005**, 87, 041109	3.4	37
179	Correlation between luminescence and compositional striations in InGaN layers grown on miscut GaN substrates. *Applied Physics Letters*, **2007**, 91, 211904	3.4	35
178	Tunneling current and electroluminescence in InGaN: Zn,Si/AlGaN/GaN blue light emitting diodes. *Journal of Electronic Materials*, **1997**, 26, 311-319	1.9	34
177	True-blue laser diodes with tunnel junctions grown monolithically by plasma-assisted molecular beam epitaxy. *Applied Physics Express*, **2018**, 11, 034103	2.4	34
176	Indium incorporation into InGaN and InAlN layers grown by metalorganic vapor phase epitaxy. *Journal of Crystal Growth*, **2011**, 318, 496-499	1.6	32
175	High power blue□violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular beam epitaxy. *Semiconductor Science and Technology*, **2005**, 20, 809-813	1.8	30
174	Cavity suppression in nitride based superluminescent diodes. *Journal of Applied Physics*, **2012**, 111, 083106	2.5	27
173	Substrate misorientation induced strong increase in the hole concentration in Mg doped GaN grown by metalorganic vapor phase epitaxy. *Applied Physics Letters*, **2008**, 93, 172117	3.4	26
172	High-Optical-Power InGaN Superluminescent Diodes with □-shaped□Waveguide. *Applied Physics Express*, **2013**, 6, 092102	2.4	25
171	Ni□Au contacts to p-type GaN □Structure and properties. *Solid-State Electronics*, **2010**, 54, 701-709	1.7	25
170	Free and bound excitons in GaN□AlGaN homoepitaxial quantum wells grown on bulk GaN substrate along the nonpolar (112□0) direction. *Applied Physics Letters*, **2005**, 86, 162112	3.4	25
169	Graded-index separate confinement heterostructure InGaN laser diodes. *Applied Physics Letters*, **2013**, 103, 261107	3.4	24
168	Application of a composite plasmonic substrate for the suppression of an electromagnetic mode leakage in InGaN laser diodes. *Applied Physics Letters*, **2009**, 95, 261108	3.4	24
167	Enhancement of optical confinement factor by InGaN waveguide in blue laser diodes grown by plasma-assisted molecular beam epitaxy. *Applied Physics Express*, **2015**, 8, 032103	2.4	23
166	Elimination of AlGaN epilayer cracking by spatially patterned AlN mask. *Applied Physics Letters*, **2006**, 88, 121124	3.4	22

165	Elimination of leakage of optical modes to GaN substrate in nitride laser diodes using a thick InGaN waveguide. *Applied Physics Express*, **2016**, 9, 092103	2.4	21
164	Lateral Control of Indium Content and Wavelength of III-Nitride Diode Lasers by Means of GaN Substrate Patterning. *Applied Physics Express*, **2012**, 5, 021001	2.4	21
163	Effect of hydrogen during growth of quantum barriers on the properties of InGaN quantum wells. *Journal of Crystal Growth*, **2015**, 414, 38-41	1.6	20
162	InGaN Laser Diode Mini-Arrays. *Applied Physics Express*, **2011**, 4, 062103	2.4	20
161	Efficient radiative recombination and potential profile fluctuations in low-dislocation InGaN/GaN multiple quantum wells on bulk GaN substrates. *Journal of Applied Physics*, **2005**, 97, 103507	2.5	20
160	Influence of hydrogen and TMIn on indium incorporation in MOVPE growth of InGaN layers. *Journal of Crystal Growth*, **2014**, 402, 330-336	1.6	19
159	Effect of efficiency droop in violet and blue InGaN laser diodes. *Applied Physics Letters*, **2009**, 95, 071108	3.4	19
158	Anomalous temperature characteristics of single wide quantum well InGaN laser diode. *Applied Physics Letters*, **2006**, 88, 071121	3.4	19
157	Spatial distribution of electron concentration and strain in bulk GaN single crystals - relation to growth mechanism. *Materials Research Society Symposia Proceedings*, **1996**, 449, 519		19
156	Continuous-wave operation of (Al,In)GaN distributed-feedback laser diodes with high-order notched gratings. *Applied Physics Express*, **2018**, 11, 112701	2.4	19
155	Hydrogen diffusion in GaN:Mg and GaN:Si. *Journal of Alloys and Compounds*, **2018**, 747, 354-358	5.7	18
154	Role of dislocation-free GaN substrates in the growth of indium containing optoelectronic structures by plasma-assisted MBE. *Journal of Crystal Growth*, **2007**, 305, 346-354	1.6	18
153	Temperature dependence of superluminescence in InGaN-based superluminescent light emitting diode structures. *Journal of Applied Physics*, **2010**, 108, 013110	2.5	17
152	GaN thin films by growth on Ga-rich GaN buffer layers. *Journal of Applied Physics*, **2000**, 88, 6032-6036	2.5	17
151	Nitride superluminescent diodes with broadened emission spectrum fabricated using laterally patterned substrate. *Optics Express*, **2016**, 24, 9673-82	3.3	17
150	True-Blue Nitride Laser Diodes Grown by Plasma-Assisted Molecular Beam Epitaxy. *Applied Physics Express*, **2012**, 5, 112103	2.4	16
149	Nitride-based quantum structures and devices on modified GaN substrates. *Physica Status Solidi (A) Applications and Materials Science*, **2009**, 206, 1130-1134	1.6	15
148	AlGaN-Free Laser Diodes by Plasma-Assisted Molecular Beam Epitaxy. *Applied Physics Express*, **2012**, 5, 022104	2.4	15

147	InGaN laser diodes operating at 450–460 nm grown by rf-plasma MBEa). *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2012**, 30, 02B102	1.3	15
146	. *Proceedings of the IEEE*, **2010**, 98, 1214-1219	14.3	15
145	Design and optimization of InGaN superluminescent diodes. *Physica Status Solidi (A) Applications and Materials Science*, **2015**, 212, 997-1004	1.6	14
144	AlGaInN laser diode technology for GHz high-speed visible light communication through plastic optical fiber and water. *Optical Engineering*, **2016**, 55, 026112	1.1	14
143	Hole carrier concentration and photoluminescence in magnesium doped InGaN and GaN grown on sapphire and GaN misoriented substrates. *Journal of Applied Physics*, **2010**, 108, 023516	2.5	14
142	Optically pumped GaN–AlGaN separate-confinement heterostructure laser grown along the (11–20) nonpolar direction. *Applied Physics Letters*, **2007**, 90, 081104	3.4	14
141	High power nitride laser diodes grown by plasma assisted molecular beam epitaxy. *Journal of Crystal Growth*, **2015**, 425, 398-400	1.6	13
140	Universal behavior of photoluminescence in GaN-based quantum wells under hydrostatic pressure governed by built-in electric field. *Journal of Applied Physics*, **2012**, 112, 053509	2.5	13
139	MBE fabrication of III-N-based laser diodes and its development to industrial system. *Journal of Crystal Growth*, **2013**, 378, 278-282	1.6	13
138	Comprehensive studies of light emission from GaN/InGaN/AlGaN single-quantum-well structures. *Journal of Crystal Growth*, **1998**, 189-190, 803-807	1.6	13
137	Band-to-band character of photoluminescence from InN and In-rich InGaN revealed by hydrostatic pressure studies. *Applied Physics Letters*, **2006**, 89, 121915	3.4	13
136	Life tests and failure mechanisms of GaN/AlGaN/InGaN light-emitting diodes **1998**,		13
135	Determination of gain in AlGaN cladding free nitride laser diodes. *Applied Physics Letters*, **2013**, 103, 061102	3.4	12
134	InAlGaN superluminescent diodes fabricated on patterned substrates: an alternative semiconductor broadband emitter. *Photonics Research*, **2017**, 5, A30	6	12
133	Ultraviolet laser diodes grown on semipolar (20–21) GaN substrates by plasma-assisted molecular beam epitaxy. *Applied Physics Letters*, **2013**, 102, 251101	3.4	12
132	Secondary ions mass spectroscopy measurements of dopant impurities in highly stressed InGaN laser diodes. *Applied Physics Letters*, **2011**, 98, 241115	3.4	12
131	Effects of high electrical stress on GaN/InGaN/AlGaN single-quantum-well light-emitting diodes. *Journal of Crystal Growth*, **1998**, 189-190, 808-811	1.6	12
130	Mode dynamics of high power (InAl)GaN based laser diodes grown on bulk GaN substrate. *Journal of Applied Physics*, **2007**, 101, 083109	2.5	12

129	InGaN laser diodes with reduced AlGaN cladding thickness fabricated on GaN plasmonic substrate. *Applied Physics Letters*, **2013**, 102, 151102	3.4	11
128	450 nm (Al,In)GaN optical amplifier with double 'j-shape' waveguide for master oscillator power amplifier systems. *Optics Express*, **2018**, 26, 7351-7357	3.3	10
127	Highly doped GaN: a material for plasmonic claddings for blue/green InGaN laser diodes **2012**,		10
126	Fabrication and properties of GaN-based lasers. *Journal of Crystal Growth*, **2008**, 310, 3979-3982	1.6	10
125	Photo-etching of GaN: Revealing nano-scale non-homogeneities. *Journal of Crystal Growth*, **2015**, 426, 153-158	1.6	9
124	Emission wavelength dependence of characteristic temperature of InGaN laser diodes. *Applied Physics Letters*, **2013**, 103, 071102	3.4	9
123	Tilt of InGaN layers on miscut GaN substrates. *Physica Status Solidi - Rapid Research Letters*, **2010**, 4, 142-144	1.5	9
122	Low dislocation density, high power InGaN laser diodes. *MRS Internet Journal of Nitride Semiconductor Research*, **2004**, 9, 1		9
121	High-power laser structures grown on bulk GaN crystals. *Journal of Crystal Growth*, **2004**, 272, 274-277	1.6	9
120	Optical and electrical characteristics of single-quantum-well InGaN light-emitting diodes. *Materials Research Society Symposia Proceedings*, **1996**, 449, 1173		9
119	Extremely long lifetime of III-nitride laser diodes grown by plasma assisted molecular beam epitaxy. *Materials Science in Semiconductor Processing*, **2019**, 91, 387-391	4.3	9
118	Influence of the growth method on degradation of InGaN laser diodes. *Applied Physics Express*, **2017**, 10, 091001	2.4	8
117	Cyan laser diode grown by plasma-assisted molecular beam epitaxy. *Applied Physics Letters*, **2014**, 104, 023503	3.4	8
116	Switching of exciton character in double InGaN/GaN quantum wells. *Physical Review B*, **2018**, 98,	3.3	8
115	Negative-T0 InGaN laser diodes and their degradation. *Applied Physics Letters*, **2015**, 106, 171107	3.4	7
114	AlGaInN laser diode technology for defence, security and sensing applications **2014**,		7
113	Why InGaN laser-diode degradation is accompanied by the improvement of its thermal stability **2008**,		7
112	Degradation of Single-Quantum Well InGaN Green Light Emitting Diodes Under High Electrical Stress. *Materials Research Society Symposia Proceedings*, **1996**, 449, 1179		7

111	Waveguide Design for Long Wavelength InGaN Based Laser Diodes. *Acta Physica Polonica A*, **2012**, 122, 1031-1033	0.6	7
110	Screening of quantum-confined Stark effect in nitride laser diodes and superluminescent diodes. *Applied Physics Express*, **2019**, 12, 044001	2.4	7
109	High speed visible light communication using blue GaN laser diodes **2016**,		6
108	Suppression of extended defects propagation in a laser diodes structure grown on (20-21) GaN. *Semiconductor Science and Technology*, **2016**, 31, 035001	1.8	6
107	Capture kinetics at deep-level electron traps in GaN-based laser diode. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2007**, 4, 2878-2882		6
106	Strong electric field and nonuniformity effects in GaN/AlN quantum dots revealed by high pressure studies. *Applied Physics Letters*, **2006**, 89, 051902	3.4	6
105	Role of band potential roughness on the luminescence properties of InGaN quantum wells grown by MBE on bulk GaN substrates. *Physica Status Solidi (B): Basic Research*, **2006**, 243, 1614-1618	1.3	6
104	Properties of InGaN blue laser diodes grown on bulk GaN substrates. *Journal of Crystal Growth*, **2005**, 281, 107-114	1.6	6
103	Semiconductor Pressure Sensors as Seen by a Physicist. *Japanese Journal of Applied Physics*, **1993**, 32, 328	1.4	6
102	Review Review on Optimization and Current Status of (Al,In)GaN Superluminescent Diodes. *ECS Journal of Solid State Science and Technology*, **2020**, 9, 015010	2	6
101	High-resolution mirror temperature mapping in GaN-based diode lasers by thermoreflectance spectroscopy. *Japanese Journal of Applied Physics*, **2017**, 56, 020302	1.4	5
100	Aluminum-free nitride laser diodes: waveguiding, electrical and degradation properties. *Optics Express*, **2017**, 25, 33113	3.3	5
99	Optical optimization of InGaN/GaN edge-emitting lasers with reduced AlGaN cladding thickness. *Japanese Journal of Applied Physics*, **2014**, 53, 032701	1.4	5
98	Broad-area high-power CW operated InGaN laser diodes **2006**, 6133, 168		5
97	Observation of localization effects in InGaN/GaN quantum structures by means of the application of hydrostatic pressure. *Physica Status Solidi (B): Basic Research*, **2004**, 241, 3285-3292	1.3	5
96	Thin Film ZnO as Sublayer for Electric Contact for Bulk GaN with Low Electron Concentration. *Acta Physica Polonica A*, **2011**, 119, 672-674	0.6	5
95	Development of the Nitride Laser Diode Arrays for Video and Movie Projectors. *MRS Advances*, **2016**, 1, 103-108	0.7	5
94	AlGaInN laser-diode technology for optical clocks and atom interferometry **2017**,		4

93	Integrated RGB laser light module for autostereoscopic outdoor displays **2015**,		4
92	A multi-wavelength (u.v. to visible) laser system for early detection of oral cancer **2015**,		4
91	Examination of thermal properties and degradation of InGaN - based diode lasers by thermoreflectance spectroscopy and focused ion beam etching. *AIP Advances*, **2017**, 7, 075107	1.5	4
90	Assessment of laser tracking and data transfer for underwater optical communications **2014**,		4
89	Violet blue laser mini-bars. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, S837-S839		4
88	Nitride based laser diodes on substrates with patterned AlN mask. *Applied Physics Letters*, **2007**, 91, 221103	3.4	4
87	Hydrostatic pressure dependence of polarization-induced interface charge in AlGaN/GaN heterostructures determined by means of capacitance-voltage characterization. *Journal of Applied Physics*, **2006**, 100, 113712	2.5	4
86	Towards identification of degradation mechanisms in InGaN laser diodes grown on bulk GaN crystals. *Physica Status Solidi (A) Applications and Materials Science*, **2006**, 203, 1778-1782	1.6	4
85	Properties of violet laser diodes grown on bulk GaN substrates **2005**,		4
84	(GaMg)N new semiconductor grown at high pressure of nitrogen. *Journal of Crystal Growth*, **1999**, 207, 27-29	1.6	4
83	Impact of dislocations on DLTS spectra and degradation of InGaN-based laser diodes. *Microelectronics Reliability*, **2018**, 88-90, 864-867	1.2	4
82	Role of dislocations in nitride laser diodes with different indium content. *Scientific Reports*, **2021**, 11, 21	4.9	4
81	. *IEEE Sensors Journal*, **2015**, 15, 123-127	4	3
80	Direct evidence of photoluminescence broadening enhancement by local electric field fluctuations in polar InGaN/GaN quantum wells. *Japanese Journal of Applied Physics*, **2018**, 57, 020305	1.4	3
79	InAlGaN superluminescent diodes fabricated on patterned substrates: an alternative semiconductor broadband emitter: publisher's note. *Photonics Research*, **2018**, 6, 652	6	3
78	Different behavior of semipolar and polar InGaN/GaN quantum wells: Pressure studies of photoluminescence. *Physica Status Solidi (A) Applications and Materials Science*, **2011**, 208, 1526-1528	1.6	3
77	New approach to cathodoluminescence studies in application to InGaN/GaN laser diode degradation. *Journal of Microscopy*, **2009**, 236, 137-42	1.9	3
76	InGaN tapered laser diodes. *Electronics Letters*, **2012**, 48, 1232	1.1	3

75	Radiation-induced effects research in emerging photonic technologies: vertical cavity surface emitting lasers, GaN light-emitting diodes, and microelectromechanical devices **1997**,		3
74	Carrier recombination mechanisms in nitride single quantum well light-emitting diodes revealed by photo- and electroluminescence. *Journal of Applied Physics*, **2008**, 104, 094504	2.5	3
73	Investigation of polarization-induced electric field screening in InGaN light emitting diodes by means of hydrostatic pressure. *Physica Status Solidi (B): Basic Research*, **2007**, 244, 32-37	1.3	3
72	Comparison of gain in group-III-nitride laser structures grown by metalorganic vapour phase epitaxy and plasma-assisted molecular beam epitaxy on bulk GaN substrates. *Semiconductor Science and Technology*, **2007**, 22, 736-741	1.8	3
71	Screening of polarization induced electric fields in blue/violet InGaN/GaN laser diodes by Si doping in quantum barriers revealed by hydrostatic pressure. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 2303-2306		3
70	Effects of MOVPE Growth Conditions on GaN Layers Doped with Germanium. *Materials*, **2021**, 14,	3.5	3
69	Influence of hydrogen pre-growth flow on indium incorporation into InGaN layers. *Journal of Crystal Growth*, **2017**, 464, 123-126	1.6	2
68	Properties of InGaN/GaN multiquantum wells grown on semipolar (20-21) substrates with different miscuts. *Journal of Crystal Growth*, **2015**, 423, 28-33	1.6	2
67	Advances in single mode and high power AlGaInN laser diode technology for systems applications **2015**,		2
66	Surface Photochemical Corrosion as a Mechanism for Fast Degradation of InGaN UV Laser Diodes. *ACS Applied Materials & Interfaces*, **2020**, 12, 52089-52094	9.5	2
65	Highly stable GaN-based betavoltaic structures grown on different dislocation density substrates. *Solid-State Electronics*, **2020**, 167, 107784	1.7	2
64	Role of the electron blocking layer in the graded-index separate confinement heterostructure nitride laser diodes. *Superlattices and Microstructures*, **2018**, 116, 114-121	2.8	2
63	Free-space and underwater GHz data transmission using AlGaInN laser diode technology **2016**,		2
62	AlGaInN laser diode technology for systems applications **2016**,		2
61	Numerical investigation of an impact of a top gold metallization on output power of a p-up III-N-based blue-violet edge-emitting laser diode. *Opto-electronics Review*, **2015**, 23,	2.4	2
60	Cavity-Free Lasing and 2D Plasma Oscillations in Optically Excited InGaN Heterostructures. *Journal of Russian Laser Research*, **2014**, 35, 447-456	0.7	2
59	GaN substrates with variable vicinal angles for laser diode applications **2012**,		2
58	High optical power ultraviolet superluminescent InGaN diodes **2013**,		2

57	InGaN mini-laser diode arrays with cw output power of 500 mW. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2348-2350		2
56	InGaN Laser Diode Degradation. Surface and Bulk Processes. *Materials Research Society Symposia Proceedings*, **2009**, 1195, 52		2
55	Nitride laser diode arrays **2009**,		2
54	Life testing and failure analysis of GaN/AlGaN/InGaN light-emitting diodes **1997**, 3004, 113		2
53	Spontaneous and stimulated emission in quantum structures grown over bulk GaN and sapphire. *Journal of Crystal Growth*, **2005**, 281, 183-187	1.6	2
52	Localization Effects in InGaN/GaN Double Heterostructure Laser Diode Structures Grown on Bulk GaN Crystals. *Japanese Journal of Applied Physics*, **2005**, 44, 7244-7249	1.4	2
51	High-pressure investigation of InGan quantum wells. *Materials Research Society Symposia Proceedings*, **1998**, 512, 399		2
50	Tapered waveguide high power AlGaInN laser diodes and amplifiers for optical integration and quantum technologies **2017**,		2
49	GaN-based distributed feedback laser diodes for optical communications **2019**,		2
48	Deep-Level Defects in MBE-Grown GaN-Based Laser Structure. *Acta Physica Polonica A*, **2007**, 112, 331-3376		2
47	Refractive Index of Heavily Germanium-Doped Gallium Nitride Measured by Spectral Reflectometry and Ellipsometry. *Materials*, **2021**, 14,	3.5	2
46	Nitride-based laser diodes and superluminescent diodes. *Photonics Letters of Poland*, **2014**, 6,	2.1	2
45	Dynamic Device Characteristics and Linewidth Measurement of InGaN/GaN Laser Diodes. *IEEE Photonics Journal*, **2021**, 13, 1-10	1.8	2
44	Lateral grating DFB AlGaInN laser diodes for optical communications and atomic clocks.. *Journal of Physics: Conference Series*, **2017**, 810, 012053	0.3	1
43	Kinetics of the radiative and nonradiative recombination in polar and semipolar InGaN quantum wells. *Scientific Reports*, **2020**, 10, 1235	4.9	1
42	True-blue laser diodes grown by plasma-assisted MBE on bulk GaN substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 666-669		1
41	Long-term degradation of InGaN-based laser diodes: Role of defects. *Microelectronics Reliability*, **2017**, 76-77, 584-587	1.2	1
40	AlGaInN diode-laser technology for optical clocks and atom interferometry. *Journal of Physics: Conference Series*, **2017**, 810, 012052	0.3	1

39	Thermal conductivity of donor-doped GaN measured with 3ω and stationary methods. *Low Temperature Physics*, **2015**, 41, 563-566	0.7	1
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37	Unambiguous relationship between photoluminescence energy and its pressure evolution in InGaN/GaN quantum wells. *Physica Status Solidi (B): Basic Research*, **2012**, 249, 476-479	1.3	1
36	Analysis of impurity-related blue emission in Zn-doped GaN/InGaN/AlGaN double heterostructure **1996**, 2693, 97		1
35	Thermal analysis of InGaN/GaN (GaN substrate) laser diodes using transient interferometric mapping. *Microelectronics Reliability*, **2007**, 47, 1649-1652	1.2	1
34	Profiling of light emission of GaN-based laser diodes with cathodoluminescence. *Physica Status Solidi (A) Applications and Materials Science*, **2006**, 203, 1811-1814	1.6	1
33	Surface and electronic structure of Ga0.92In0.08N thin film investigated by photoelectron spectroscopy. *Thin Solid Films*, **2005**, 476, 396-404	2.2	1
32	Screening of built-in electric fields in group III-nitride laser diodes observed by means of hydrostatic pressure. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 1019-1022		1
31	Nonlinear optical characterization of single-crystalline GaN by Z-scan technique **2001**,		1
30	Luminescence of nonthermalized electron-hole plasma in GaN epilayers **2001**,		1
29	Electrical Properties of Nichia AlGaN/InGaN/GaN Blue LEDs in a Wide Current/Temperature Range. *Materials Research Society Symposia Proceedings*, **1995**, 395, 937		1
28	AlGaInN laser diode bars for high-power, optical integration and quantum technologies **2017**,		1
27	GaN laser diodes for quantum technologies **2017**,		1
26	High Power Continuous Wave Blue InAlGaN Laser Diodes Made by Plasma Assisted MBE. *Acta Physica Polonica A*, **2006**, 110, 345-351	0.6	1
25	Material Issues in GaN-based Laser Diode Manufacturing **2019**,		1
24	InGaN blue light emitting micro-diodes with current path defined by tunnel junction. *Optics Letters*, **2020**, 45, 4332-4335	3	1
23	Recent progress in distributed feedback InGaN/GaN laser diodes **2019**,		1
22	InGaN Laser Diode Degradation **2013**, 247-261		1

21	GaN Laser Diode Technology for Visible-Light Communications. *Electronics (Switzerland)*, **2022**, 11, 1430	2.6	1
20	Impact of thermal crosstalk between emitters on power roll-over in nitride-based blue-violet laser bars. *Semiconductor Science and Technology*, **2017**, 32, 025008	1.8	0
19	The influence of the sapphire substrate on the temperature dependence of the GaN bandgap. *Materials Research Society Symposia Proceedings*, **1999**, 572, 289		0
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